

MOTOROLA

**SEMICONDUCTOR**

TECHNICAL DATA

**MC54/74HCT240A**

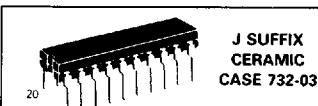
# Octal 3-State Inverting Buffer/ Line Driver/Line Receiver with LSTTL-Compatible Inputs

## High-Performance Silicon-Gate CMOS

The MC54/74HCT240A is identical in pinout to the LS240. This device may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT240A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has inverting outputs and two active-low output enables.

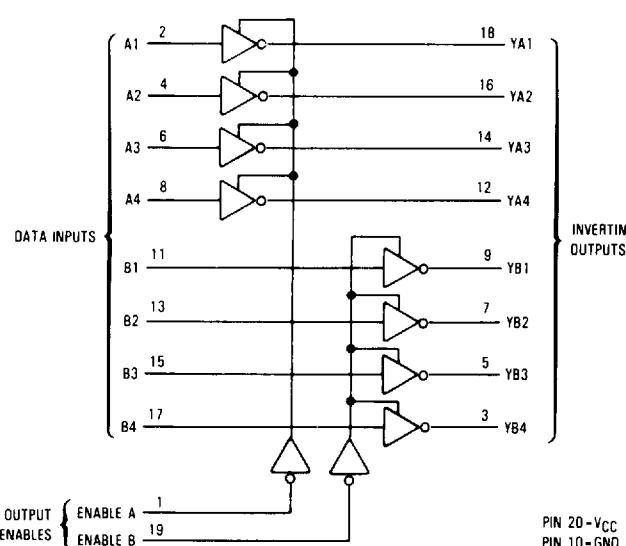
The HCT240A is the inverting version of the HCT244. See also HCT241.

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1  $\mu$ A
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 110 FETs or 27.5 Equivalent Gates

**ORDERING INFORMATION**

MC74HCTXXXAN	Plastic
MC54HCTXXXAJ	Ceramic
MC74HCTXXXADW	SOIC

$T_A = -55^\circ$  to  $125^\circ\text{C}$  for all packages.  
Dimensions in Chapter 6.

**LOGIC DIAGRAM****PIN ASSIGNMENT**

ENABLE A	1	●	20	V <sub>CC</sub>
A1	2	19	ENABLE B	
YB4	3	18	YA1	
A2	4	17	B4	
YB3	5	16	YA2	
A3	6	15	B3	
YB2	7	14	YA3	
A4	8	13	B2	
YB1	9	12	YA4	
GND	10	11	B1	

**FUNCTION TABLE**

Inputs	Outputs	
Enable A, Enable B	A, B	Y <sub>A</sub> , Y <sub>B</sub>
L	L	H
L	H	L
H	X	Z

Z = High Impedance

X = Don't Care

## MC54/74HCT240A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	-0.5 to +7	V
$V_{in}$	DC Input Voltage (Referenced to GND)	-1.5 to $V_{CC} + 1.5$	V
$V_{out}$	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
$I_{in}$	DC Input Current, per Pin	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 35$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq V_{in} \text{ or } V_{out} \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating – Plastic DIP: -10 mW/°C from 65° to 125°C

Ceramic DIP: -10 mW/°C from 100° to 125°C

SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

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## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
$V_{in-V_{out}}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	$V_{CC}$	V
$T_A$	Operating Temperature, All Package Types	-55	+125	°C
$t_r, t_f$	Input Rise and Fall Time (Figure 1)	0	500	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	$V_{CC}$ V	Guaranteed Limit			Unit
				$\geq -55^{\circ}\text{C}$	$\leq 85^{\circ}\text{C}$	$\leq 125^{\circ}\text{C}$	
$V_{IH}$	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5 5.5	2 2	2 2	2 2	V
$V_{IL}$	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
$V_{OH}$	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \approx 6 \text{ mA}$	4.5	3.98	3.84	3.7	
$V_{OL}$	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \leq 20 \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \approx 6 \text{ mA}$	4.5	0.26	0.33	0.4	
$I_{in}$	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or } GND$	5.5	$\pm 0.1$	$\pm 1$	$\pm 1$	μA
$I_{OZ}$	Maximum Three-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	5.5	$\pm 0.5$	$\pm 5$	$\pm 10$	μA
$I_{CC}$	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \mu\text{A}$	5.5	4	40	160	μA

$\Delta I_{CC}$	Additional Quiescent Supply Current	$V_{in} = 2.4 \text{ V, Any One Input}$ $V_{in} = V_{CC} \text{ or } GND, \text{ Other Inputs}$ $I_{out} = 0 \mu\text{A}$		$\geq -55^{\circ}\text{C}$	$25^{\circ}\text{C to } 125^{\circ}\text{C}$	
			5.5	2.9	2.4	mA

## NOTES:

- Information on typical parametric values along with frequency or heavy load considerations can be found in Chapter 4.
- Total Supply Current =  $I_{CC} + \sum \Delta I_{CC}$ .

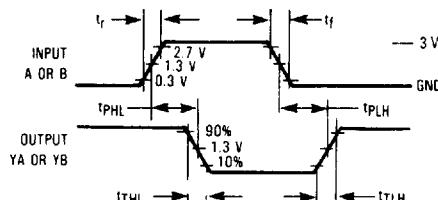
AC ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5.0 \text{ V} \pm 10\%$ ,  $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

Symbol	Parameter	Guaranteed Limit			Unit
		$25^\circ\text{C}$ to $-55^\circ\text{C}$	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
$t_{PLH}$ , $t_{PHL}$	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	20	25	30	ns
$t_{PLZ}$ , $t_{PHZ}$	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	28	35	42	ns
$t_{PZL}$ , $t_{PZH}$	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	25	31	38	ns
$t_{TLH}$ , $t_{THL}$	Maximum Output Transition Time, Any Output (Figures 1 and 3)	12	15	18	ns
$C_{in}$	Maximum Input Capacitance	10	10	10	pF
$C_{out}$	Maximum Three-State Output Capacitance (Output in High-Impedance State)	15	15	15	pF

CPD	Power Dissipation Capacitance (Per Enabled Output) Used to determine the no-load dynamic power consumption: $P_D = CPD V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4 subject listing on page 4-2.	Typical @ $25^\circ\text{C}$ , $V_{CC} = 5 \text{ V}$		pF
		55		

NOTE: 1. For propagation delays with loads other than 50 pF and information on typical parametric values and load considerations, see Chapter 4.

## SWITCHING WAVEFORMS



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Figure 1.

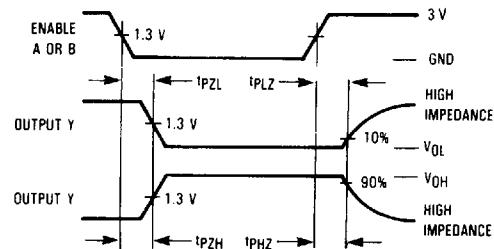
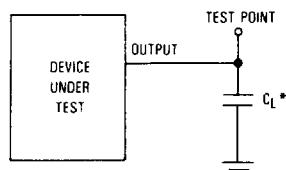
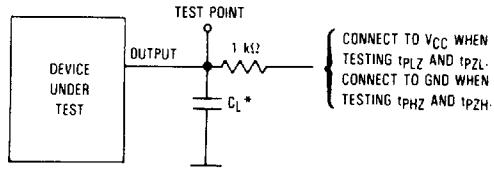


Figure 2.



\*Includes all probe and jig capacitance.

Figure 3. Test Circuit



\*Includes all probe and jig capacitance.

Figure 4. Test Circuit

## LOGIC DETAIL

